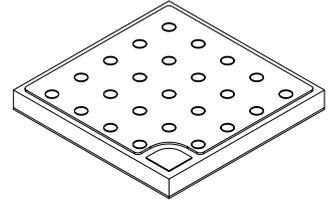


ODB4040UX3.A2

OS-CORE® UX:3



Features:

- Polarity: p-side up
- Chip technology: UX:3
- Color: • blue
- Chipsize: 40 mil x 40 mil

Ordering Information

Type
ODB4040UX3.A2-MM-MM-1-C

Ordering Code
Q65111A5240

Maximum Ratings

Parameter	Symbol		Values
Operating Temperature	T_{op}	min.	-40 °C
		max.	135 °C
Storage Temperature ¹⁾	T_{stg}	min.	-40 °C
		max.	135 °C
Recommended Die Storage Temperature ≤ 60% RH	$T_{stg\ die}$	max.	30 °C
Junction Temperature	T_j	max.	150 °C
Junction temperature for short time applications*	T_j	max.	175 °C
Forward Current $T_j = 25\text{ °C}$	I_F	min.	20 mA
		max.	1500 mA
Forward Current Pulsed $t \leq 10\ \mu\text{s}$; $D = 0.005$; $T_j = 25\text{ °C}$	$I_{F\ pulse}$	max.	2500 mA
Reverse voltage ²⁾ $T_j = 25\text{ °C}$	V_R	max.	5 V
ESD withstand voltage acc. ANSI/ESDA/JEDEC JS-001 (HBM, Class 0)	V_{ESD}		ESD sensitive device

*The median lifetime (L70/B50) for $T_j = 175\text{ °C}$ is 100h.

Characteristics

$I_F = 350\text{ mA}$; $T_j = 25\text{ °C}$

Parameter	Symbol		Values
Dominant Wavelength ³⁾ $I_F = 350\text{ mA}$	λ_{dom}	min.	440.0 nm
		max.	480.0 nm
Forward Voltage ⁴⁾ $I_F = 350\text{ mA}$	V_F	min.	2.70 V
		typ.	2.85 V
		max.	3.20 V

Additional Information

Die bonding	Metalization frontside	Metalization backside
Adhesive bonding	Gold	Gold

Binning Table ⁵⁾³⁾

$I_F = 350 \text{ mA}$

Radiant Intensity I_e a. u.	Dominant Wavelength λ_{dom} nm				
	440.0 - 442.5	442.5 - 445.0	445.0 - 447.5	447.5 - 450.0	450.0 - 452.5
100 - 105	A16	B16	C16	D16	E16
105 - 107	A19	B19	C19	D19	E19
107 - 110	A22	B22	C22	D22	E22
110 - 114	A25	B25	C25	D25	E25
114 - 117	A28	B28	C28	D28	E28
117 - 120	A31	B31	C31	D31	E31
120 - 124	A34	B34	C34	D34	E34
124 - 128	A37	B37	C37	D37	E37
128 - 132	A40	B40	C40	D40	E40
132 - 136	A43	B43	C43	D43	E43
136 - 140	A46	B46	C46	D46	E46

Radiant Intensity I_e a. u.	Dominant Wavelength λ_{dom} nm			
	452.5 - 455.0	455.0 - 457.5	457.5 - 460.0	460.0 - 462.5
100 - 105	F16	G16	H16	I16
105 - 107	F19	G19	H19	I19
107 - 110	F22	G22	H22	I22
110 - 114	F25	G25	H25	I25
114 - 117	F28	G28	H28	I28
117 - 120	F31	G31	H31	I31
120 - 124	F34	G34	H34	I34
124 - 128	F37	G37	H37	I37
128 - 132	F40	G40	H40	I40
132 - 136	F43	G43	H43	I43
136 - 140	F46	G46	H46	I46

Correlation factor ⁶⁾

Unit	Value	Condition
CF (mW/sr / a.u.)	1.6	chip to air
CF (mW / a.u.)	5.25	chip with silicone lens

Binning Table ⁵⁾³⁾

$I_F = 350 \text{ mA}$

Luminous Intensity Dominant Wavelength

I_v a. u.	λ_{dom} nm				
	462.5 - 465.0	465.0 - 467.5	467.5 - 470.0	470.0 - 472.5	472.5 - 475.0
45 - 50	J10	K10	L10	M10	N10
50 - 55	J13	K13	L13	M13	N13
55 - 60	J16	K16	L16	M16	N16
60 - 65	J19	K19	L19	M19	N19
65 - 70	J22	K22	L22	M22	N22
70 - 75	J25	K25	L25	M25	N25
75 - 80	J28	K28	L28	M28	N28
80 - 90	J31	K31	L31	M31	N31

Luminous Intensity

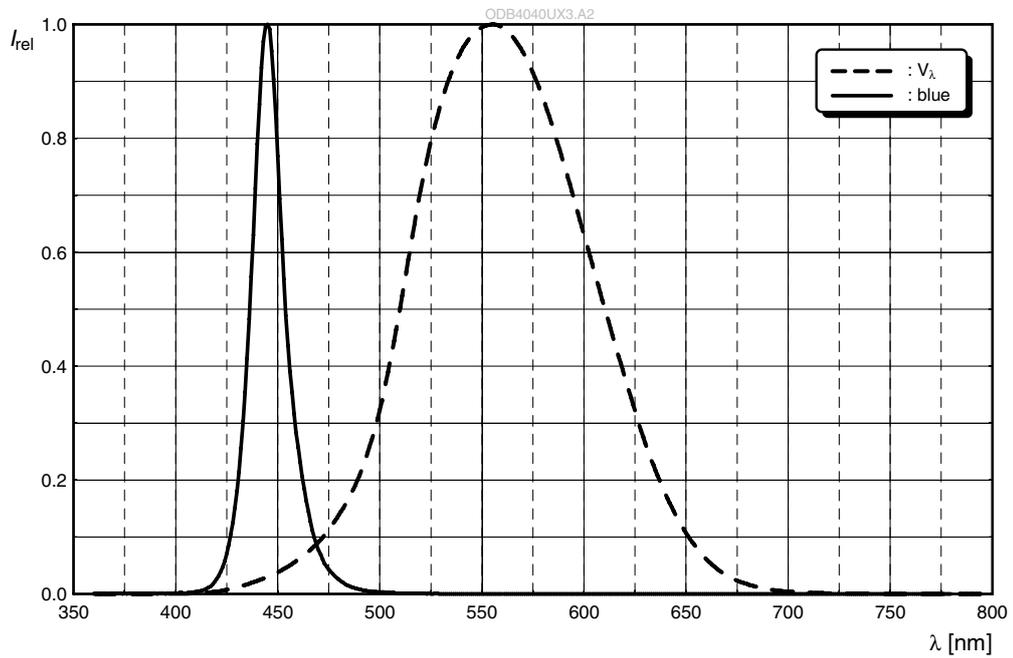
I_v a. u.	Dominant Wavelength	
	λ_{dom} nm	
	475.0 - 477.5	477.5 - 480.0
45 - 50	O10	P10
50 - 55	O13	P13
55 - 60	O16	P16
60 - 65	O19	P19
65 - 70	O22	P22
70 - 75	O25	P25
75 - 80	O28	P28
80 - 90	O31	P31

Correlation factor ⁶⁾

Unit	Value	Condition
CF (mcd / a.u.)	160	chip to air
CF (mlm / a.u.)	535	chip with silicone lens

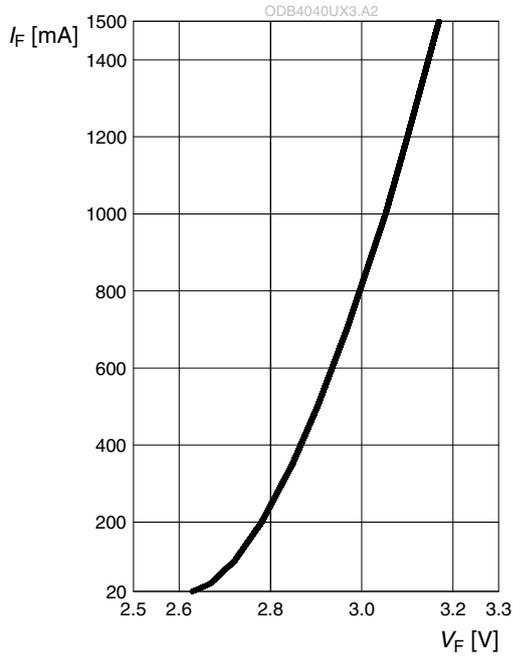
Relative Spectral Emission ⁷⁾

$I_{rel} = f(\lambda)$; $I_F = 350 \text{ mA}$; $T_S = 25 \text{ °C}$



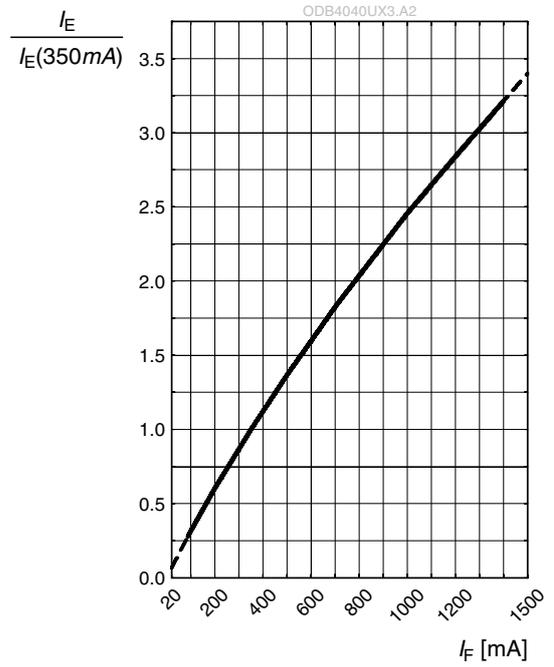
Forward current 7), 8)

$I_F = f(V_F); T_S = 25\text{ °C}$



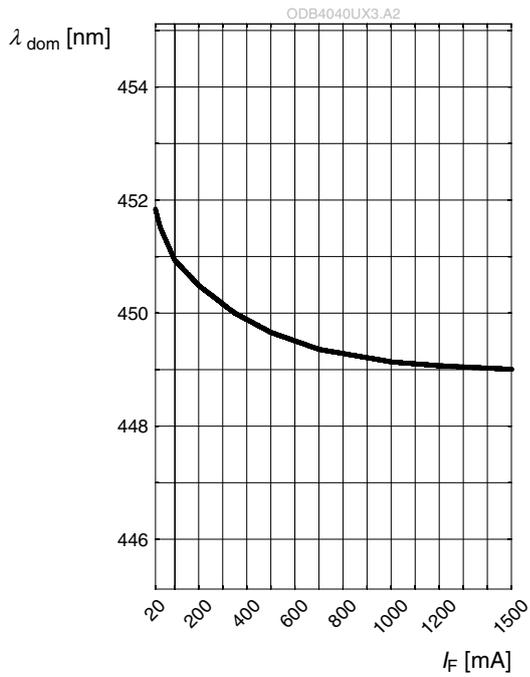
Relative Radiant Intensity 7), 8)

$I_E/I_E(350\text{ mA}) = f(I_F); T_S = 25\text{ °C}$



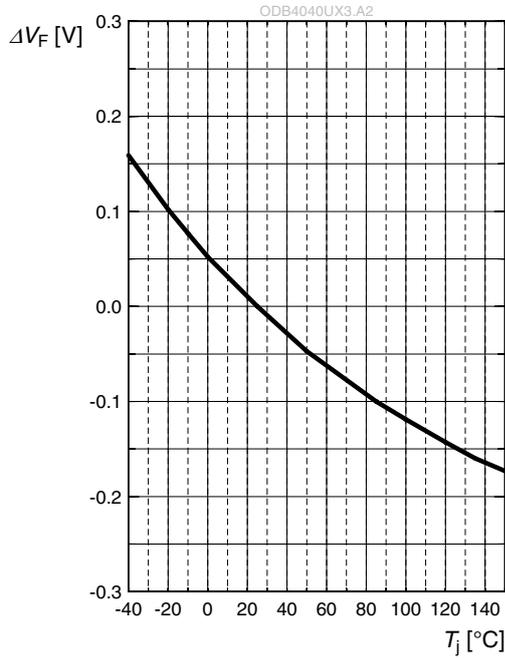
Dominant Wavelength 7)

$\lambda_{\text{dom}} = f(I_F); T_S = 25\text{ °C}$



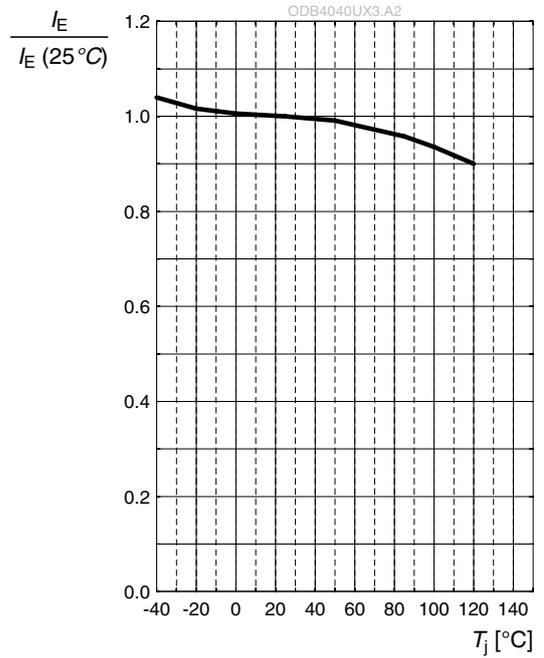
Forward Voltage ⁷⁾

$$\Delta V_F = V_F - V_F(25\text{ }^\circ\text{C}) = f(T_j); I_F = 350\text{ mA}$$



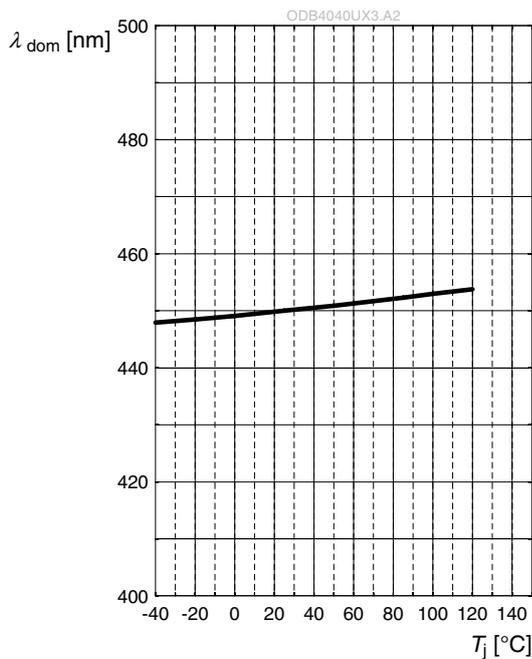
Relative Radiant Intensity ⁷⁾

$$I_E/I_E(25\text{ }^\circ\text{C}) = f(T_j); I_F = 350\text{ mA}$$



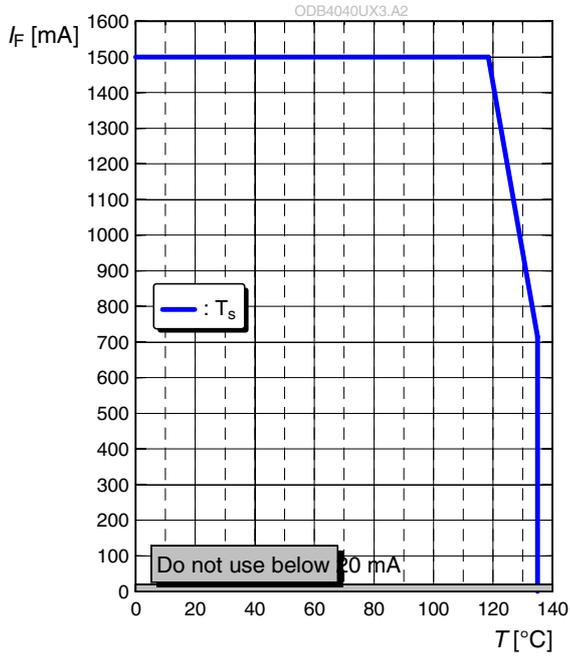
Dominant Wavelength ⁷⁾

$$\lambda_{\text{dom}} = f(T_j); I_F = 350\text{ mA}$$



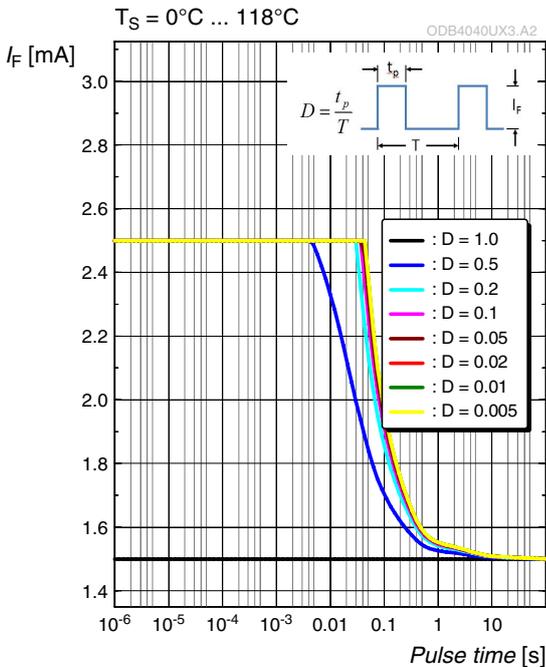
Max. Permissible Forward Current

$I_F = f(T)$



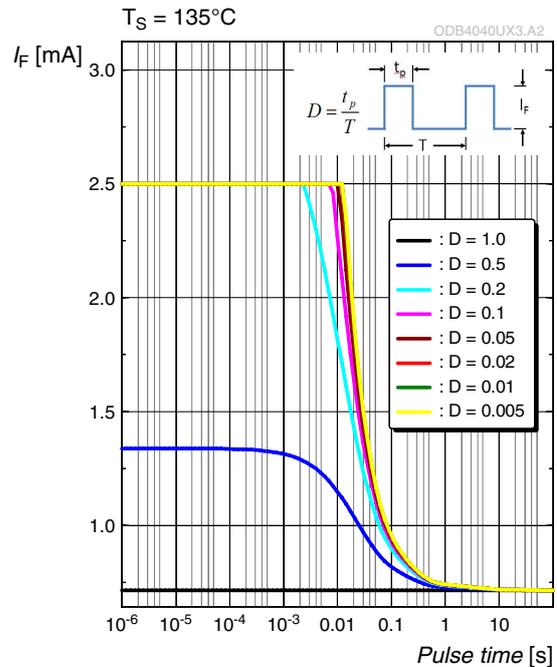
Permissible Pulse Handling Capability

$I_F = f(t_p)$; D: Duty cycle

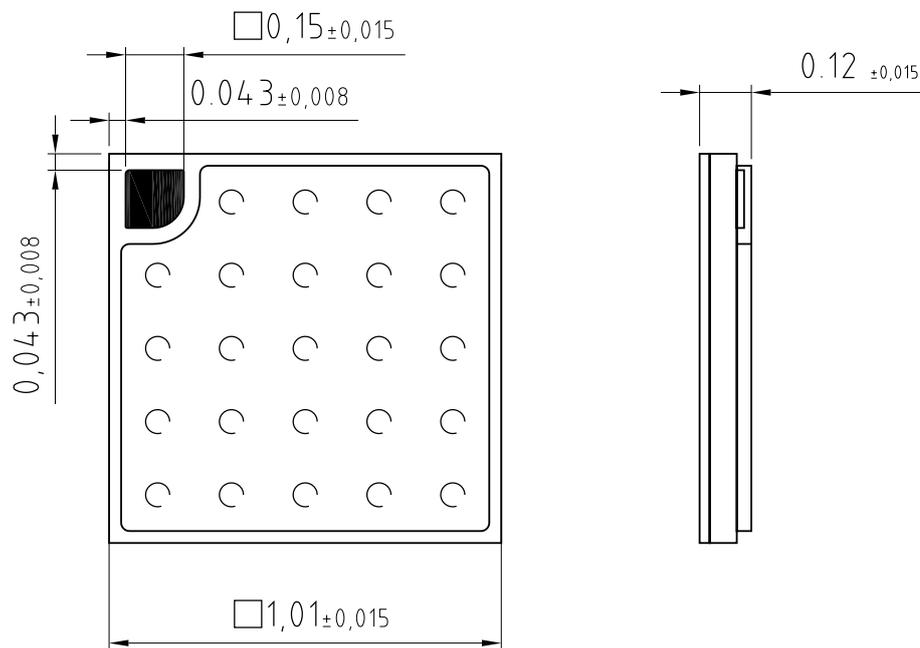


Permissible Pulse Handling Capability

$I_F = f(t_p)$; D: Duty cycle



Dimensional Drawing ⁹⁾



ODB4040UX3.A2

Disclaimer

Disclaimer

Language english will prevail in case of any discrepancies or deviations between the two language wordings.

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Glossary

- 1) **Shelf life:** Temperature refer solely to storage of finished LED product (Not valid for chip on die sheet).
- 2) **Reverse Operation:** Reverse Operation of 10 hours is permissible in total. Continuous reverse operation is not allowed.
- 3) **Wavelength:** The wavelength is measured at a current pulse of typically 10 ms and with an internal reproducibility of ± 1 nm (with a coverage factor of $k = 3$).
- 4) **Forward Voltage:** The forward voltage is measured during a current pulse of typically 5 ms and with an internal reproducibility of ± 0.1 V (with a coverage factor of $k = 3$).
- 5) **Brightness:** Brightness values are measured during a current pulse of typically 10 ms and with an internal reproducibility of ± 8 % (with a coverage factor of $k = 3$).
- 6) **Correlation Factor:** The exemplary correlation factor (CF) was estimated by sample build of the chip in a reference package and describes the exemplary correlation between the chip brightness measured in arbitrary units (a.u.) and the brightness in a reference package: $CF = I/\Phi(\text{package}) / I(\text{chip})$. This factor is purely given as an indication of possible package brightness values. It may vary for different packages due to influences of geometries, reflectivity/refractive index of package materials or other material properties.
- 7) **Typical Values:** Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- 8) **Characteristic curve:** In the range where the line of the graph is broken, you must expect higher differences between single devices within one packing unit.
- 9) **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with ± 0.1 and dimensions are specified in mm.

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